



RFLM-102402Q(E/F)-290

PIN Diode L & S Band Ultra Low Leakage Limiter Module - SMT

Features:

- Frequency Range: 1.0 to 4.0 GHz
- High Average Power Handling: +50 dBm
- High Peak Power Handling: +60 dBm
- Low Insertion Loss: <0.5 dB
- Return Loss: >17 dB
- Low Flat Leakage Power: <14 dBm
- Low Spike Energy Leakage: <0.5 ergs
- Package: 8mm x 5mm x 2.5mm
- Input & Output DC Coupling Capacitors
- No external control lines or power supply required
- RoHS Compliant

Description:

The RFLM-102402QF-290 SMT Silicon PIN Diode Limiter Module offer both High Power CW and Peak protection across the L & S-Band region. It is based on proven hybrid assembly technique utilized extensively in high reliability, mission critical applications. The RFLM-102402QF-290 offers excellent thermal characteristics in a compact, low profile 8mm x 5mm x 2.5mm package. The RFLM-102402QF-290 is designed for optimal small signal insertion loss permitting extremely low receiver noise figure while simultaneously offering excellent large input signal Flat Leakage for effective receiver protection in the S Band frequency range.

The RFLM-102402QF-290 Limiter Module provides outstanding passive receiver protection (Always On) which protects against High Average Power up to +50 dBm (CW), High Peak Power up to +60 dBm pulsed, maintains low flat leakage to less than +14 dBm (typ) and reduces Spike Leakage to less than 0.5 ergs.

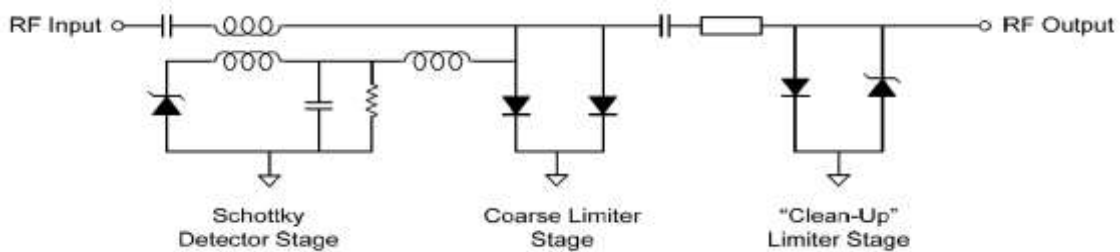
ESD and Moisture Sensitivity Rating

The RFLM-102402QF-290 Limiter Module carries a Class 0 ESD rating (HBM) and an MSL 1 moisture rating.

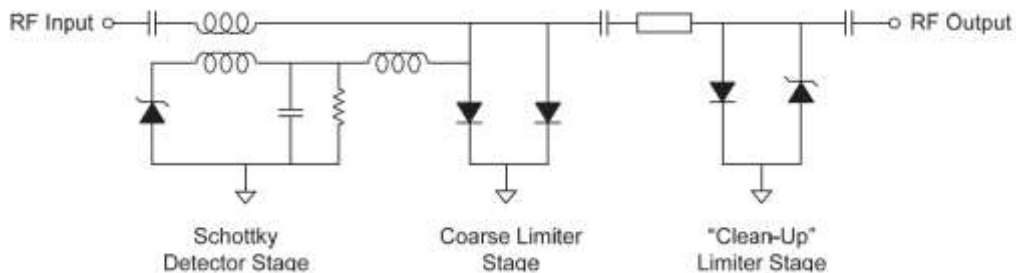
Thermal Management Features

The RFLM-102402QF-290 based substrate has been design to offer superior long term reliability in the customer's application by utilizing ultra-thin Au plating to combat Au embrittlement concerns. Also, a proprietary design methodology has minimized the thermal resistance from the PIN Diode junction to base plate (R_{THJ-A}). The two stage limiter design employs a second stage Schottky and quarter wavelength spacer detector circuit which permits ultra-fast turn on of the High Power PIN Diodes. This circuit topology couple with the thermal characteristic of the substrate design enables reliably handling High Input RF Power up to +50 dBm CW and RF Peak Power levels up to +60 dBm (25 uSec pulse width @ 1.0% duty cycle with base plate temperature at +85°C). The I layer of the PIN diodes have been selected to produce a flat leakage of 15dBm typical and a spike leakage of 0.5 ergs typical.

RFLM-102402QE-290 Limiter Module Schematic - with Input & RF Coupling Capacitor Only



RFLM-102402QF-290 Limiter Module Schematic - with Input & Output RF Coupling Capacitors



Absolute Maximum Ratings

@ $Z_0=50\Omega$, $T_A=+25^\circ\text{C}$ as measured on the base ground surface of the device.

| Parameter | Conditions | Absolute Maximum Value |
|---|---|------------------------|
| Operating Temperature | | -65°C to 125°C |
| Storage Temperature | | -65°C to 150°C |
| Junction Temperature | | 175°C |
| Assembly Temperature | T = 30 seconds | 260°C |
| RF Peak Incident Power | $T_{\text{CASE}}=85^\circ\text{C}$, source and load VSWR < 1.2:1, RF Pulse width = 25 usec, duty cycle = 5%, derated linearly to 0 W at $T_{\text{CASE}}=150^\circ\text{C}$ (See note 1) | 60 dBm |
| RF CW Incident Power | $T_{\text{CASE}}=85^\circ\text{C}$, source and load VSWR < 1.2:1, derated linearly to 0 W at $T_{\text{CASE}}=150^\circ\text{C}$ (See note 1) | 50 dBm |
| RF Input & Output DC Block Capacitor Voltage Breakdown | | 100 V DC |

Note 1: T_{CASE} is defined as the temperature of the bottom ground surface of the device.

RFLM102402QF-290 Electrical Specifications

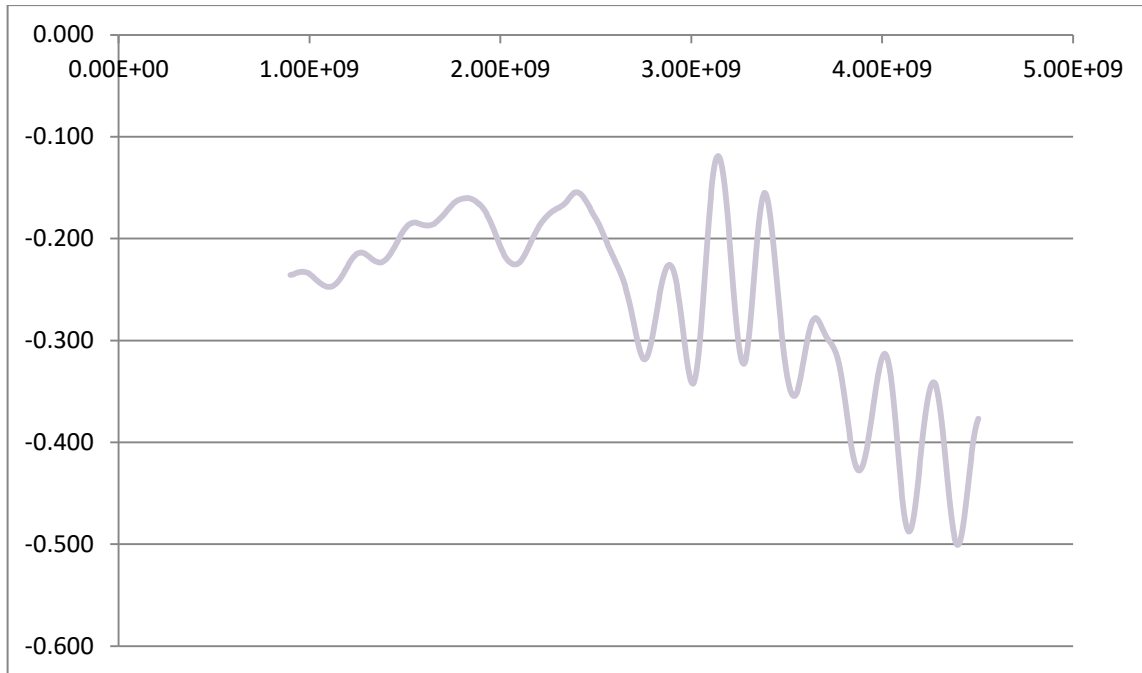
@ $Z_0=50\Omega$, $T_A=+25^\circ\text{C}$ as measured on the base ground surface of the device.

| Parameters | Symbol | Test Conditions | Min Value | Typ Value | Max Value | Units |
|--|--------------------------|---|-----------|-----------|-----------|-------|
| Frequency | F | $1\text{ GHz} \leq F \leq 4\text{ GHz}$ | 1.0 | | 4.0 | GHz |
| Insertion Loss | IL | $1\text{ GHz} \leq F \leq 4\text{ GHz}$, $P_{\text{in}} = -20\text{ dBm}$ | | 0.35 | 0.45 | dB |
| Insertion Loss Rate of Change vs Operating Temperature | ΔIL | $1\text{ GHz} \leq F \leq 4\text{ GHz}$, $P_{\text{in}} \leq -20\text{ dBm}$ | | 0.005 | | dB/°C |
| Return Loss | RL | $1\text{ GHz} \leq F \leq 4\text{ GHz}$, $P_{\text{in}} = -20\text{ dBm}$ | 16 | 17 | | dB |
| Input 1 dB Compression Point | $\text{IP}_{1\text{dB}}$ | $1\text{ GHz} \leq F \leq 4\text{ GHz}$ | | 8 | | dBm |
| 2 nd Harmonic | $2F_0$ | $P_{\text{in}} = -10\text{ dBm}$, $F_0 = 3.0\text{ GHz}$ | | -40 | -30 | dBc |
| Peak Incident Power | $P_{\text{inc(PK)}}$ | RF Pulse = 25 usec, duty cycle = 5%, $t_{\text{rise}} \leq 2\text{ us}$, $t_{\text{fall}} \leq 2\text{ usec}$ | | | 60 | dBm |
| CW Incident Power | $P_{\text{inc(CW)}}$ | $1\text{ GHz} \leq F \leq 4\text{ GHz}$ | | | 50 | dBm |
| Flat Leakage | FL | $P_{\text{in}} = 60\text{ dBm}$, RF Pulse width = 25 us, duty cycle = 5%, $t_{\text{rise}} \leq 2\text{ us}$, $t_{\text{fall}} \leq 2\text{ us}$ | | 14 | 15 | dBm |
| Spike Leakage | SL | $P_{\text{in}} = 60\text{ dBm}$, RF Pulse width = 25 us, duty cycle = 5% | | 0.5 | 0.7 | erg |
| Recovery Time | T_R | 50% falling edge of RF Pulse to 1 dB IL, $P_{\text{in}} = 50\text{ dBm}$ peak, RF PW = 25 us, duty cycle = 5%, $t_{\text{rise}} \leq 2\text{ us}$, $t_{\text{fall}} \leq 1\text{ usec}$ | | 1.0 | 1.5 | usec |

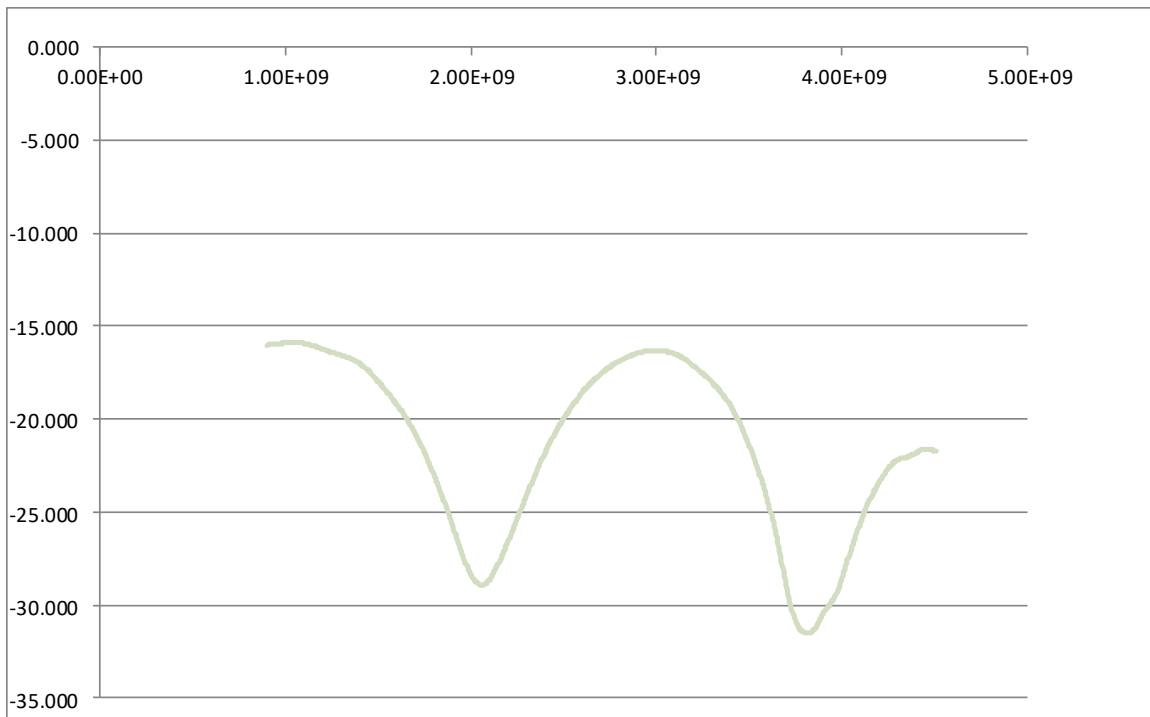
RFLM-102402QF-290 Typical Performance

$Z_0 = 50\Omega$, $T_{CASE} = +25^\circ C$, PIN = -20 dBm as measured on the Ground Plane of the device.

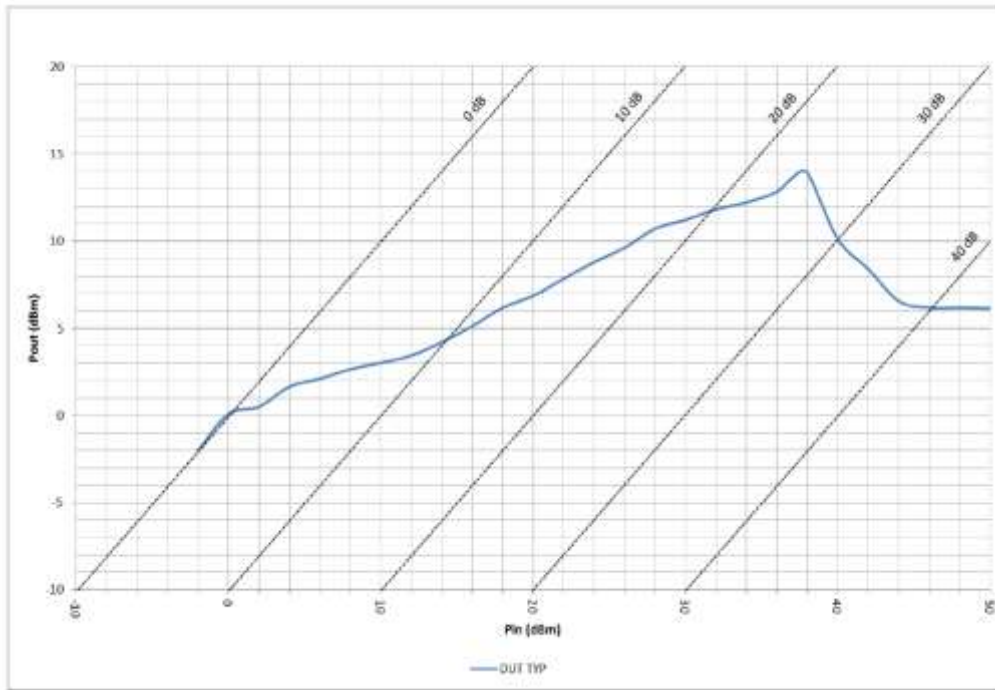
RFLM-102402QE/F-290: Insertion Loss vs Frequency



RFLM-102402QE/F-290: Return Loss vs Frequency



RFLM-102402QE/F-290: Pin vs Pout

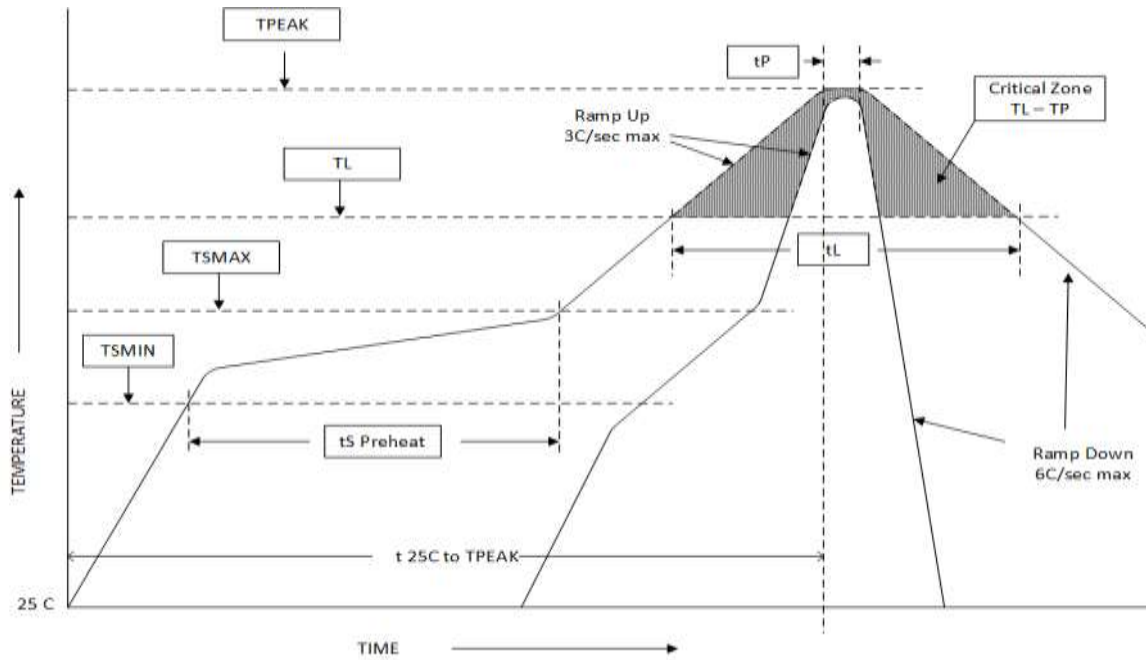


Assembly Instructions

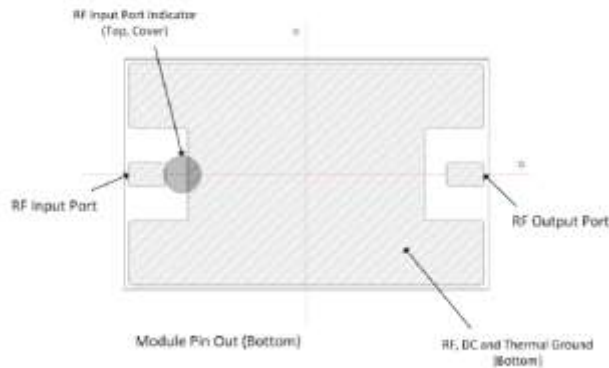
The RFLM-102402QF-290 may be attached to the printed circuit card using solder reflow procedures using either RoHS or Sn63/ Pb37 type solders per the Table and Temperature Profile Graph shown below:

| Profile Parameter | Sn-Pb Assembly Technique | RoHS Assembly Technique |
|---|--------------------------|-------------------------|
| Average ramp-up rate (T_L to T_P) | 3°C/sec (max) | 3°C/sec (max) |
| Preheat | | |
| Temp Min (T_{smin}) | 100°C | 100°C |
| Temp Max (T_{smax}) | 150°C | 150°C |
| Time (min to max) (t_s) | 60 – 120 sec | 60 – 120 sec |
| T_{smax} to T_L | | |
| Ramp up Rate | | 3°C/sec (max) |
| Peak Temp (T_P) | 225°C +0°C / -5°C | 260°C +0°C / -5°C |
| Time within 5°C of Actual Peak Temp (T_P) | 10 to 30 sec | 20 to 40 sec |
| Time Maintained Above: | | |
| Temp (T_L) | 183°C | 217°C |
| Time (t_L) | 60 to 150 sec | 60 to 150 sec |
| Ramp Down Rate | 6°C/sec (max) | 6°C/sec (max) |
| Time 25°C to T_P | 6 minutes (max) | 8 minutes (max) |

Solder Re-Flow Time-Temperature Profile



RFLM-102402QE/F-290 Limiter Module Package Outline Drawing



Notes:

- 1) Metalized area on backside is the RF, DC and Thermal ground. In user's end application this surface temperature must be managed to meet the power handling requirements.
- 2) Back side metallization is thin Au termination plating to combat Au embrittlement (Au plated over Cu).
- 3) Unit = mils

Thermal Design Considerations:

The design of the RFLM-102402QF-290 Limiter Module permits the maximum efficiency in thermal management of the PIN Diodes while maintaining extremely high reliability. Optimum Limiter performance and reliability of the device can be achieved by the maintaining the base ground surface temperature of less than 85°C.

There must be a minimal thermal and electrical resistance between the limiter module and ground. Adequate thermal management is required to maintain a T_{jc} at less than +175°C and thereby avoid adversely affecting the semiconductor reliability. Special care must be taken to assure that minimal voiding occurs in the solder connection in the areas shade in red in the figure shown below.

